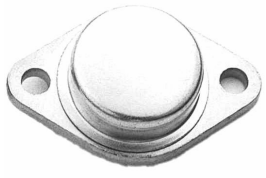
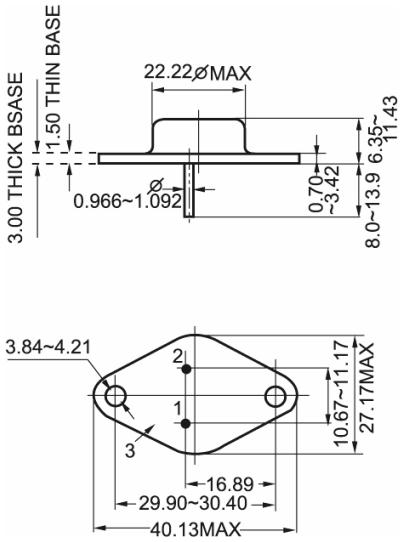
2N3055

Silicon NPN Transistors



◆ Features

• Designed for general-purpose switching and amplifier applications
• With TO-3 package
• Complementary to MJ2955



TO-3

◆ Absolute Maximum Ratings Tc=25℃

SYMBOL	PARAMETER	RATING	UNIT
V_{CBO}	Collector to base voltage	100	V
V_{CEO}	Collector to emitter voltage	60	V
V_{EBO}	Emitter to base voltage	7.0	V
I_{CP}	Peak collector current		A
I_C	Collector current	15	A
P_C	Collector power dissipation	115	W
T_j	Junction temperature	200	℃
T_{stg}	Storage temperature	-65~200	℃

◆ Electrical Characteristics Tc=25℃

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
I_{CBO}	Collector-base cut-off current	V_{CB}=100V,$V_{BE(off)}$=1.5V		1.0	mA
I_{EBO}	Emitter-base cut-off current	V_{EB} = 7V; I_C=0		5.0	mA
I_{CEO}	Collector-emitter cut-off current	V_{CE}=30V,I_B=0		0.7	mA
V_{CBO}	Collector-base breakdown voltage				
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=200mA,I_B=0	60		V
V_{EBO}	Emitter-base breakdown voltage				
$V_{CEsat-1}$	Collector-emitter saturation voltages	I_C = 4A; I_B = 0.4A		1.1	V
$V_{CEsat-2}$	Collector-emitter saturation voltages	I_C = 10A; I_B = 3.3A		3.0	V
$V_{CEsat-3}$	Collector-emitter saturation voltages				
$V_{CEsat-4}$	Collector-emitter saturation voltages				
h_{FE-1}	Forward current transfer ratio	I_C=4A,V_{CE}=4V	20	150	
h_{FE-2}	Forward current transfer ratio	I_C=10A,V_{CE}=4V	5.0		
h_{FE-3}	Forward current transfer ratio	I_C=0.2A,V_{CE}=4V	60	250	
h_{FE-4}	Forward current transfer ratio				
$V_{BE(sat)1}$	Base-emitter saturation voltages	I_C=4A,V_{CE}=4V		1.5	V
$V_{BE(sat)2}$	Base-emitter saturation voltages				
$V_{BE(sat)3}$	Base-emitter saturation voltages				
f_T	Transition frequency at f = 1MHz	I_C=0.5A,V_{CE}=10V	2.5		MHz
t_f	Fall time				
t_s	Tum-off storage time				